DESCRIPTION

The 2SA1797-P, 2SA1797-Q, and 2SA1797-R are available in the SOT-89 package.

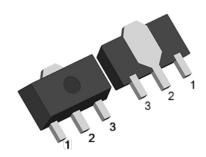
FEATURE

- Low saturation voltage. V_{CE(sat)}=-0.35V(Max.) at I_C / I_B=-1A/-50mA.
- Excellent DC current gain characteristics.
- · Complementary the 2SC4672.

ORDERING INFORMATION

Package Type	Part Number		
	2SA1797-P		
SOT-89	2SA1797-Q		
	2SA1797-R		
SPQ	1,000pcs/Reel		
AiT provides all RoHS Compliant Products			

PIN DESCRIPTION



SOT-89

hFE CLASSIFICATION

Rank	Range
Р	82 ~ 180
Q	120 ~ 270
R	180 ~ 390

PIN#	DESCRIPTION		
1	Base		
2	Collector		
3	Emitter		

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise specified.

V _{CEO} , Collector-Emitter Voltage	-50 V
V _{CBO} , Collector-Base Voltage	-50 V
V _{EBO} , Emitter-Base Voltage	-6 V
Ic, Collector Current	-1.5 A
Pc, Collector Power Dissipation	0.5 W
T _J , Junction Temperature	150 °C
T _{stg} , Storage Temperature	-55 ~ +150 °C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

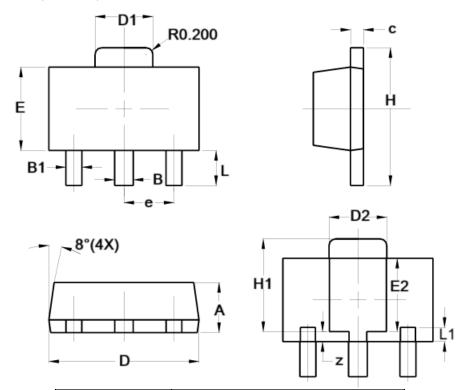
ELECTRICAL CHARACTERISTICS

 T_A =25°C unless otherwise specified.

Parameter	Symbols	Conditions	Min.	Тур.	Max.	Unit
Collector-Emitter Breakdown Voltage	BVcEo	I _C = -1 mA	-50	-	-	V
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = -50 μA	-50	-	-	V
Emitter-Base Breakdown Voltage	BV _{EBO}	Ι _Ε = -50 μΑ	-6	-	-	V
Collector Cutoff Current	Ісво	V _{CB} = -50 V	-	1	-0.1	μΑ
Emitter Cutoff Current	I _{EBO}	V _{EB} = -5 V	-	-	-0.1	μΑ
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_{C} = -1 \text{ A},$ $I_{B} = -50 \text{ mA},$	-	-0.15	-0.35	V
DC Current transfer ratio	h _{FE}	V _{CE} = -2 V, I _C = -0.5 A	82	-	390	-
Transition Frequency	f⊤	$V_{CE} = -2 \text{ V},$ $I_{C} = -0.5 \text{ A}$ $f = 100 \text{ MHz}$	-	200	-	MHz
Collector Output Capacitance	C _{ob}	$V_{CB} = -10 \text{ V},$ $I_E = 0 \text{ A}$ $f = 1 \text{ MHz}$	-	36	50	pF

PACKAGE INFORMATION

Dimension in SOT-89 (Unit: mm)



Complete I	Millin	Millimeter		
Symbol	Min.	Max.		
Α	1.400	1.600		
В	0.500	0.620		
B1	0.420	0.540		
С	0.350	0.430		
D	4.440	4.600		
D1	1.620	1.830		
D2	1.610	1.810		
Е	2.400	2.600		
E2	2.050	2.350		
е	1.500 TYP.			
Н	3.950	4.250		
H1	2.630	2.930		
L	0.900	1.200		
L1	0.327	0.527		
Z	0.200	0.400		

2SA1797
TRANSISTOR
SILICON PNP TYPE TRANSISTOR

IMPORTANT NOTICE

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